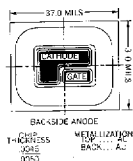


SCRs

0.5 Amp, Planar

JAN & JANTX 2N3027-2N3032



FEATURES

- JAN and JANTX Types Available
- Fully Characterized for "Worst Case" Design
- Passivated Planar Construction for Maximum Reliability and Parameter Uniformity
- Low On-State Voltage and Fast Switching at High Current Levels
- Typical Turn-On Time: 0.12μs
- Typical Recovery Time: 0.1μs
- Pulse Currents: to 30A

DESCRIPTION

The 2N3027 series of planar SCRs (controlled switches) are intended for use in military and space applications requiring a high degree of reliability. They offer a unique combination of extremely fast switching, precise triggering, high pulse power, small size, intrinsic parameter stability, and high radiation tolerance.

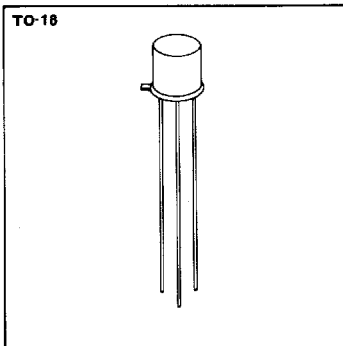
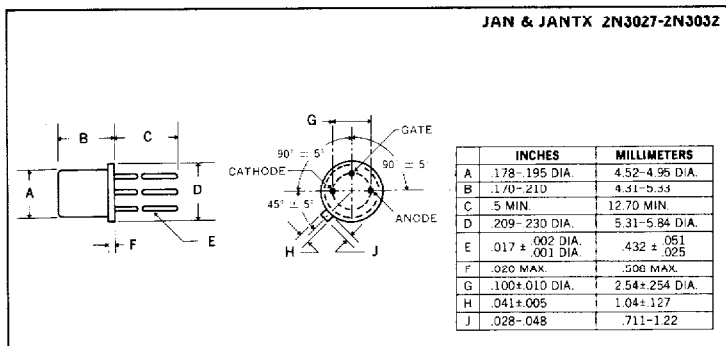
The JAN and JANTX types are specified under MIL-S-19500/419, and are included in MIL-STD-701 as recommended types for military usage.

ABSOLUTE MAXIMUM RATINGS

	JAN & JANTX 2N3027 JAN & JANTX 2N3030	JAN & JANTX 2N3028 JAN & JANTX 2N3031	JAN & JANTX 2N3029 JAN & JANTX 2N3032
Repetitive Peak Off-State Voltage, V_{DRM}	30V	60V	100V
Repetitive Peak Reverse Voltage, V_{RRM}	30V	60V	100V
D.C. On-State Current, I_T			
100°C Case		500mA	
75°C Ambient		250mA	
Repetitive Peak On-State Current, I_{TSM}		30A	
Surge (Non-Rep.) On-State Current, I_{TSM}			
50ms		5A	
8ms		8A	
Peak Gate Current, I_{GM}		250mA	
Average Gate Current, $I_{G(AV)}$		25mA	
Reverse Gate Voltage		5V	
Reverse Gate Current		3mA	
Storage Temperature Range		-65°C to +200°C	
Operating Temperature Range		-65°C to +150°C	

Note: Blocking voltage ratings apply over the operating temperature range, provided the gate is connected to the cathode through an appropriate resistor, or adequate gate bias is used. (See section on bias stabilization.)

MECHANICAL SPECIFICATIONS



Microsemi Corp.
Watertown
The diode experts

ELECTRICAL SPECIFICATIONS (at 25°C unless noted) 2N3027 — 2N3028 — 2N3029

Parameter	Symbol	Min.	Typical	Max.	Units	Test Conditions
SUBGROUP 1 Visual and Mechanical	—	—	—	—	—	MIL-STD-750 Method 2071
SUBGROUP 2 (25°C Tests) Off-State Current Reverse Current Reverse Gate Voltage Gate Trigger Current Gate Trigger Voltage On-State Voltage Holding Current	I_{DRM} I_{RRM} V_{GR} I_{GT} V_{GT} V_T I_H	— — 5 -5 .40 0.8 0.3	.002 .002 0 8 .55 1.2 0.7	0.1 0.1 — 200 .80 1.5 5.0	μA μA V μA V V mA	$R_{GK} = 1K, V_{DRM} = \text{Rating}$ $R_{GK} = 1K, V_{RRM} = \text{Rating}$ $I_{GR} = 0.1mA$ $R_{GS} = 10K, V_D = 5V$ $R_{GS} = 100\Omega, V_D = 5V$ $I_T = 1A$ (pulse test) $R_{GK} = 1K, V_D = 5V$
SUBGROUP 3 (25°C Tests) Off-State Voltage — Critical Rate of Rise Gate Trigger-on Pulse Width Delay Time Rise Time Circuit Commutated Turn-off Time	dv_e/dt $t_{pg(on)}$ t_d t_r t_q	30 15 10 — — —	60 30 25 .07 .08 .04 0.7	— — — — — 2.0	V/ μs μs μs μs μs	$R_{GK} = 1K, V_D = 30V$ (2N3027) $R_{GK} = 1K, V_D = 60V$ (2N3028) $R_{GK} = 1K, V_D = 100V$ (2N3029) $I_G = 10mA, I_T = 1A, V_{DM} = 30V$ $I_G = 10mA, I_T = 1A, V_D = 30V$ $I_G = 10mA, I_T = 1A, V_D = 30V$ $I_T = 1A, I_H = 1A, R_{GK} = 1K$
SUBGROUP 4 (150°C Tests) High Temp. Off-State Current High Temp. Reverse Current High Temp. Gate Trigger Voltage High Temp. Holding Current	I_{DRM} I_{RRM} V_{GT} I_H	— — .10 .05	2 20 .15 .20	20 50 0.6 1.0	μA μA V mA	$R_{GK} = 1K, V_{DRM} = \text{Rating}$ $R_{GK} = 1K, V_{RRM} = \text{Rating}$ $R_{GS} = 100\Omega, V_D = 5V$ $R_{GK} = 1K, V_D = 5V$
SUBGROUP 5 (-65°C Tests) Low Temp. Gate Trigger Voltage Low Temp. Gate Trigger Current Low Temp. Holding Current	V_{GT} I_{GT} I_H	0.6 0 0.5	0.75 150 3.5	1.1 1.2 10	V mA mA	$R_{GS} = 100\Omega, V_D = 5V$ $R_{GS} = 10K, V_D = 5V$ $R_{GK} = 1K, V_D = 5V$

ELECTRICAL SPECIFICATIONS (at 25°C unless noted) 2N3030 — 2N3031 — 2N3032

Parameter	Symbol	Min.	Typical	Max.	Units	Test Conditions
SUBGROUP 1 Visual and Mechanical	—	—	—	—	—	MIL-STD-750 Method 2071
SUBGROUP 2 (25°C Tests) Off-State Current Reverse Current Reverse Gate Voltage Gate Trigger Current Gate Trigger Voltage On-State Voltage Holding Current	I_{DRM} I_{RRM} V_{GR} I_{GT} V_{GT} V_T I_H	— — 5 -5 0.44 0.8 0.3	.002 .002 8 20 0.6 1.2 1.0	0.1 0.1 — 20 0.6 1.5 4.0	μA μA V μA V V mA	$R_{GK} = 1K, V_{DRM} = \text{Rating}$ $R_{GK} = 1K, V_{RRM} = \text{Rating}$ $I_{GR} = 0.1mA$ $R_{GS} = 10K, V_D = 5V$ $R_{GS} = 100\Omega, V_D = 5V$ $I_T = 1A$ (pulse test) $R_{GK} = 1K, V_D = 5V$
SUBGROUP 3 (25°C Tests) Off-State Voltage — Critical Rate of Rise Gate Trigger-on Pulse Width Delay Time Rise Time Circuit Commutated Turn-off Time	dv_e/dt $t_{pg(on)}$ t_d t_r t_q	30 15 10 — — —	60 30 25 .05 .01 .05 0.7	— — — — — 2.0	V/ μs μs μs μs μs	$R_{GK} = 1K, V_D = 30V$ (2N3030) $R_{GK} = 1K, V_D = 60V$ (2N3031) $R_{GK} = 1K, V_D = 100V$ (2N3032) $I_G = 10mA, I_T = 1A, V_D = 30V$ $I_G = 10mA, I_T = 1A, V_D = 30V$ $I_G = 10mA, I_T = 1A, V_D = 30V$ $I_T = 1A, I_H = 1A, R_{GK} = 1K$
SUBGROUP 4 (150°C Tests) High Temp. Off-State Current High Temp. Reverse Current High Temp. Gate Trigger Voltage High Temp. Holding Current	I_{DRM} I_{RRM} V_{GT} I_H	— — .10 .05	2 20 .15 .30	20 50 0.4 2.0	μA μA V mA	$R_{GK} = 1K, V_{DRM} = \text{Rating}$ $R_{GK} = 1K, V_{RRM} = \text{Rating}$ $R_{GS} = 100\Omega, V_D = 5V$ $R_{GK} = 1K, V_D = 5V$
SUBGROUP 5 (-65°C Tests) Low Temp. Gate Trigger Voltage Low Temp. Gate Trigger Current Low Temp. Holding Current	V_{GT} I_{GT} I_H	0.44 0 0.5	0.8 0.4 5.0	0.95 0.5 8	V mA mA	$R_{GS} = 100\Omega, V_D = 5V$ $R_{GS} = 10K, V_D = 5V$ $R_{GK} = 1K, V_D = 5V$

High Reliability Processing

The 2N3027-2N3032 series provides a complete range of high reliability processing from the standard devices that undergo extensive electrical testing, through JAN and JANTX levels. 100% processing, Group B, and Group C tests for JAN and JANTX devices is shown below. For further details, see MIL-S-19500/419(EL).

100% Screening TX-Types

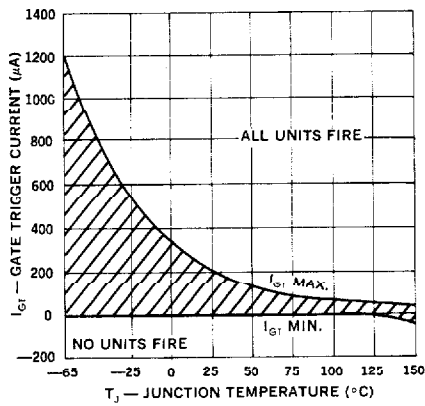
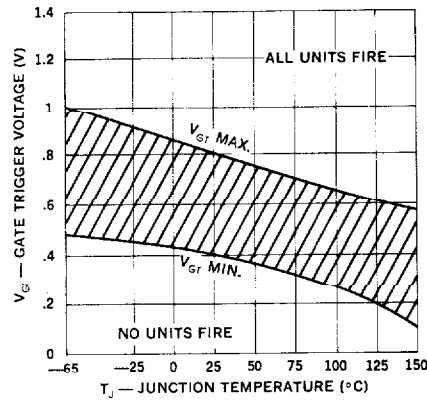
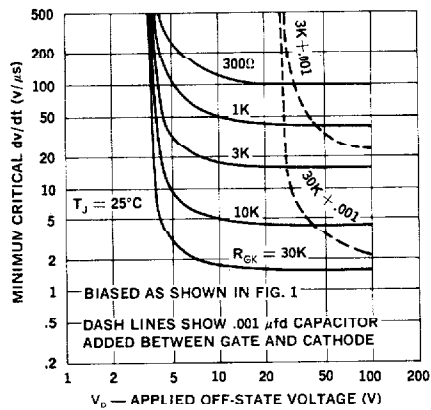
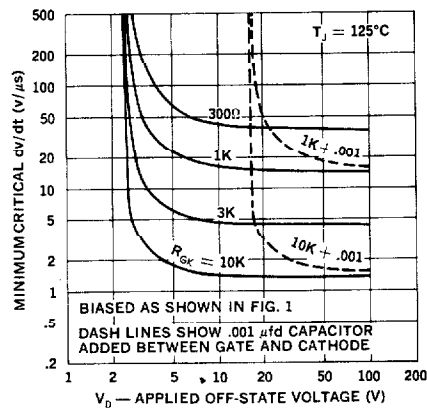
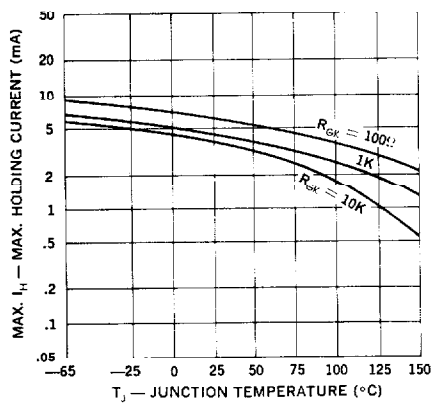
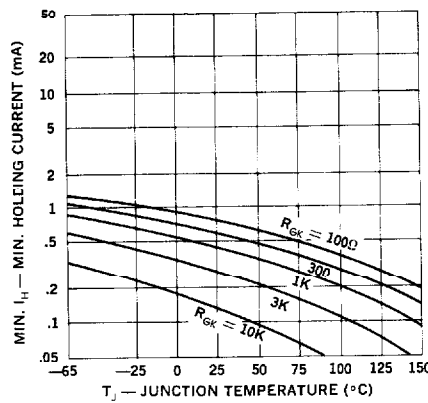
High Temperature Storage
Temperature Cycling
Constant Acceleration
Fine & Gross Hermetic Seal
Electrical Test
Burn-in
Electrical Test

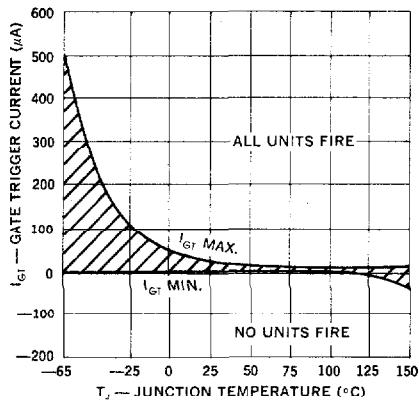
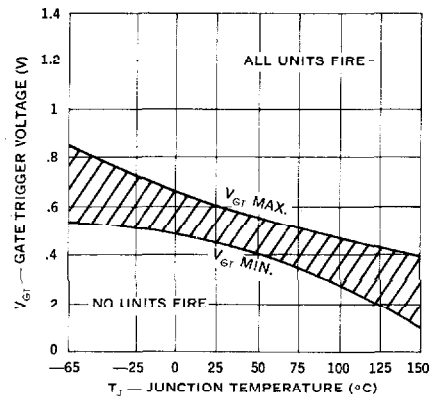
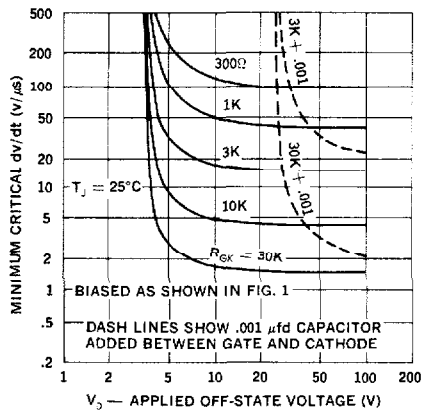
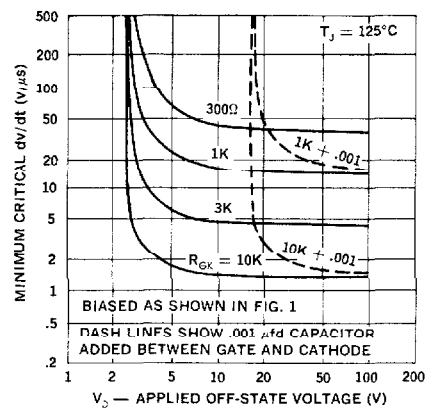
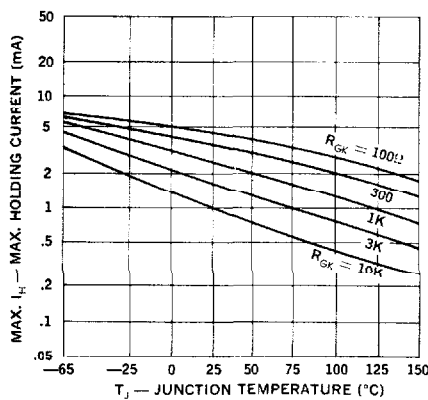
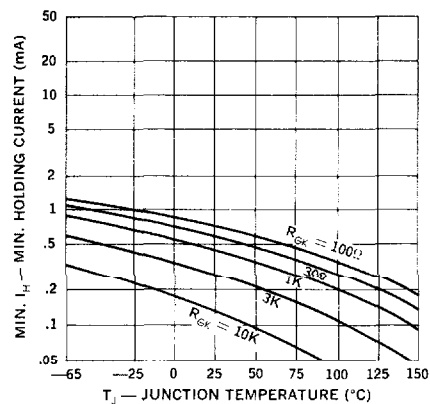
Group B Tests

Subgroup 1 — Physical Dimensions
Subgroup 2 — Solderability
Temperature Cycling
Thermal Shock
Constant Acceleration
Moisture Resistance
Subgroup 3 — Surge Current
Subgroup 4 — Blocking Life Test
Subgroup 5 — Storage Life Test
Subgroup 6 — Operating Life Test

Group C Tests

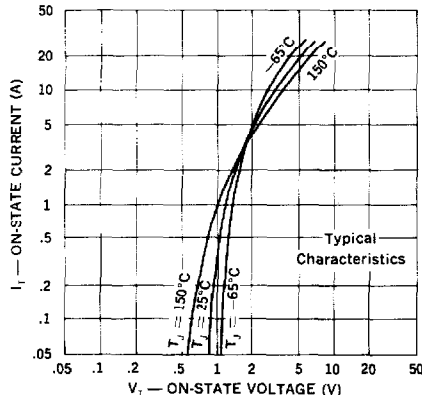
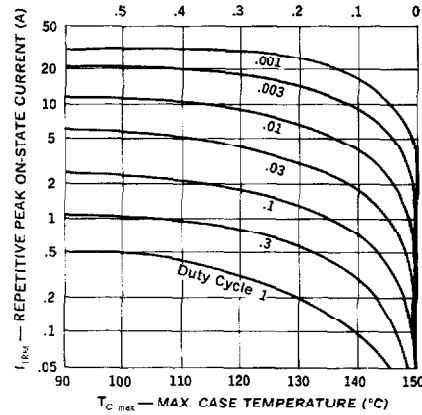
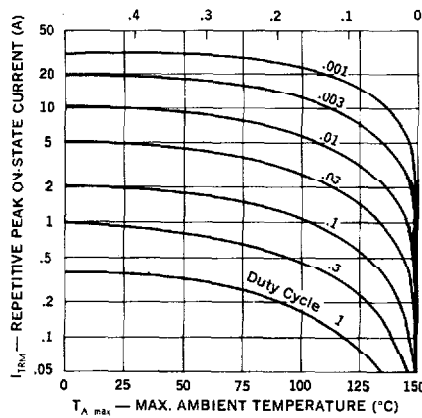
Subgroup 1 — Shock
Vibration, Variable Frequency
Subgroup 2 — Salt Atmosphere
Subgroup 3 — Terminal Strength
Subgroup 4 — High Temp. Anode Voltage — Critical rate or rise
Subgroup 5 — Storage Life Test
Subgroup 6 — Operating Life Test

TYPICAL CHARACTERISTICS
2N3027 — 2N3028 — 2N3029
1 Gate Trigger Current**2 Gate Trigger Voltage****3 Min. Critical dv/dt (25°C — R Bias)****4 Min. Critical dv/dt (125°C — R Bias)****5 Max. Holding Current (Resistor Bias)****6 Min. Holding Current (Resistor Bias)**

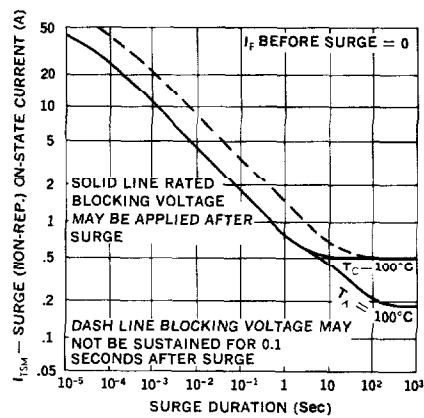
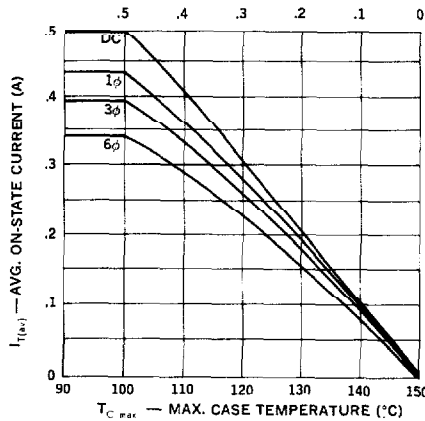
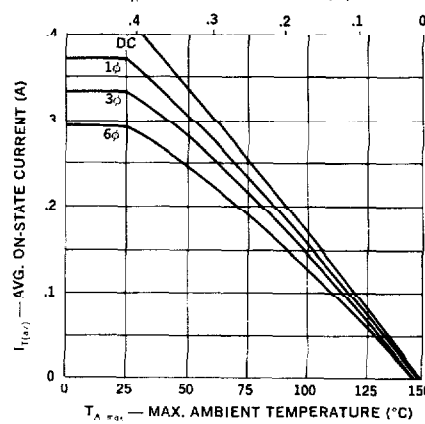
TYPICAL CHARACTERISTICS
2N3030 — 2N3031 — 2N3032
1 Gate Trigger Current**2 Gate Trigger Voltage****3 Min. Critical dv/dt (25°C — R Bias)****4 Min. Critical dv/dt (125°C — R Bias)****5 Max. Holding Current (Resistor Bias)****6 Min. Holding Current (Resistor Bias)**

CURRENT RATINGS

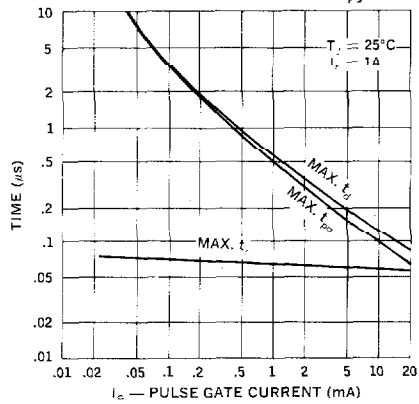
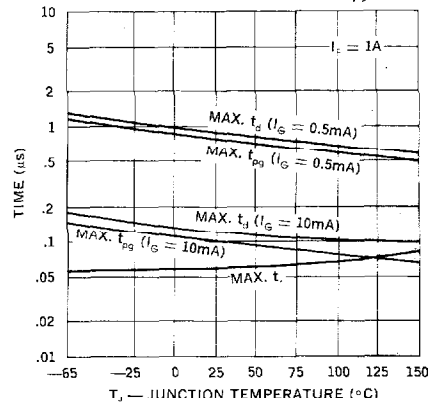
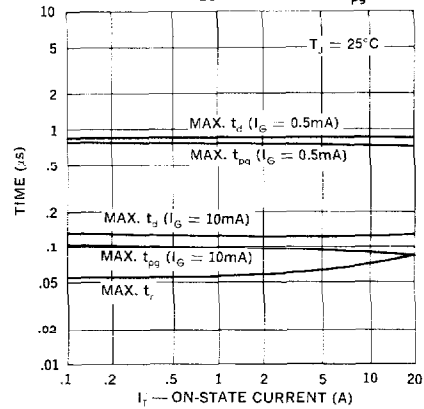
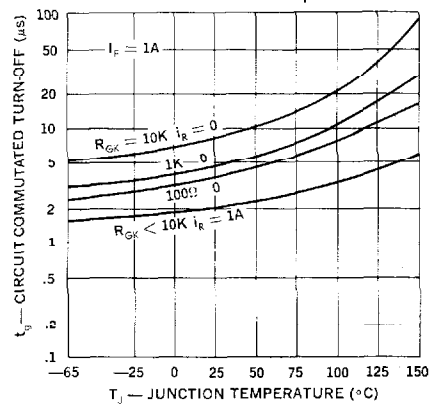
C1 Forward on Current vs. Voltage

C2 Peak Current vs. Case Temperature
 P_A — POWER DISSIPATION (W)C3 Peak Current vs. Ambient Temperature
TO-18 Ratings (see note)
 P_A — POWER DISSIPATION (W)

C4 Surge Current vs. Time

C5 Average Current vs. Case Temperature
 P_A — POWER DISSIPATION (W)C6 Average Current vs. Ambient Temperature
TO-18 Ratings (see note)
 P_A — POWER DISSIPATION (W)

SWITCHING SPEEDS

S1 Maximum Delay Time t_d , Rise Time t_r , and Gate Trigger Pulse Width t_{pg} (on)S2 Maximum Delay Time t_d , Rise Time t_r , and Gate Trigger Pulse Width t_{pg} (on)S3 Maximum Delay Time t_d , Rise Time t_r , and Gate Trigger Pulse Width t_{pg} (on)S4 Maximum Circuit Commutated Turn-off Time t_q S5 Maximum Circuit Commutated Turn-off Time t_q 